

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|------------------------------|-----------|-------|------|
| Collector-Base Voltage | V_{CBO} | 50 | V |
| Collector-Emitter Voltage | V_{CEO} | 30 | V |
| Emitter-Base Voltage | V_{EBO} | 5 | V |
| Peak Pulse Current | I_{CM} | 2 | A |
| Continuous Collector Current | I_C | 1 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------------|--------------------|
| Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ | P_D | 600 | mW |
| Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$ | $R_{\theta JA}$ | 209 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Notes: 3. Device mounted on FR-4 PCB MRP

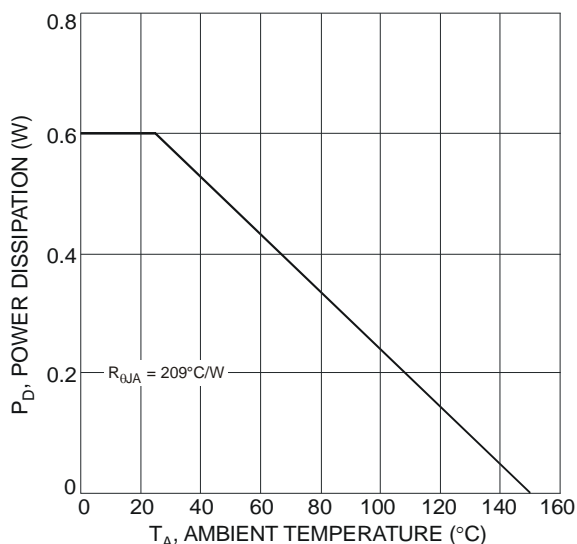


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

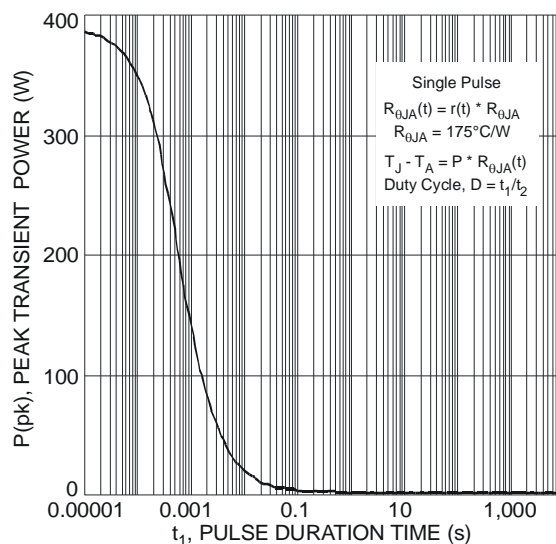


Fig. 2 Single Pulse Maximum Power Dissipation

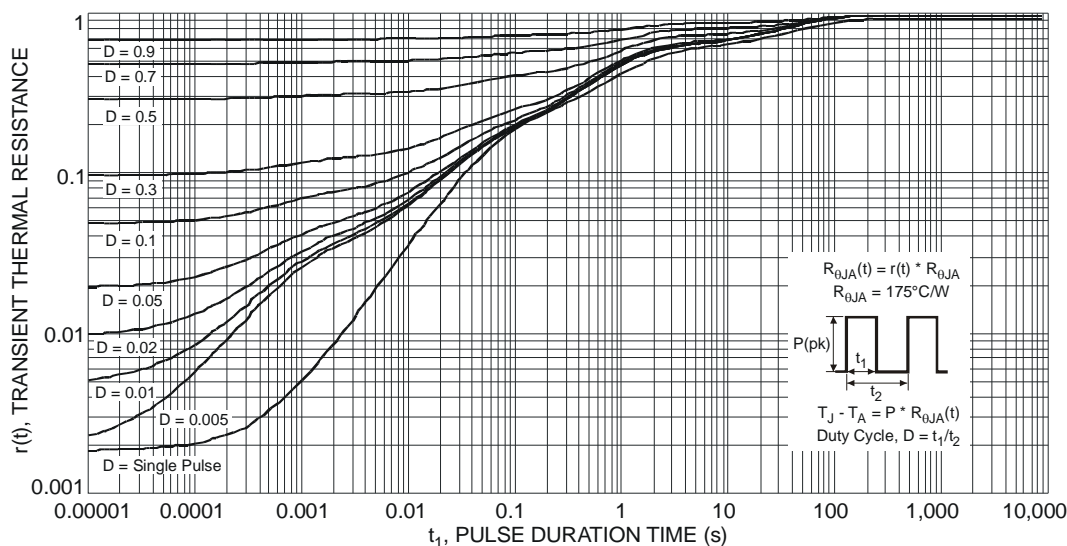


Fig. 3 Transient Thermal Response

Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|----------------------|-----|------|-----|------|---|
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | 50 | — | — | V | I _C = 100μA |
| Collector-Emitter Breakdown Voltage (Note 4) | V _{(BR)CEO} | 30 | — | — | V | I _C = 10mA |
| Emitter-Base Breakdown Voltage | V _{(BR)EBO} | 5 | — | — | V | I _E = 100μA |
| Collector-Base Cutoff Current | I _{CBO} | — | — | 100 | nA | V _{CB} = 30V, I _E = 0 |
| | | — | — | 50 | μA | V _{CB} = 30V, I _E = 0, T _A = 150°C |
| Emitter-Base Cutoff Current | I _{EBO} | — | — | 100 | nA | V _{EB} = 4V, I _C = 0 |
| DC Current Gain (Note 4) | h _{FE} | 300 | — | — | — | V _{CE} = 5V, I _C = 50mA |
| | | 300 | 450 | 900 | | V _{CE} = 5V, I _C = 0.5A |
| | | 200 | — | — | | V _{CE} = 5V, I _C = 1A |
| Collector-Emitter Saturation Voltage (Note 4) | V _{CE(sat)} | — | — | 75 | mV | I _C = 0.1A, I _B = 1mA |
| | | — | — | 125 | | I _C = 0.5A, I _B = 50mA |
| | | — | — | 200 | | I _C = 1.0A, I _B = 100mA |
| Equivalent On-Resistance (Note 4) | R _{CE(sat)} | — | — | 200 | mΩ | I _E = 1A, I _B = 100mA |
| Base-Emitter Saturation Voltage (Note 4) | V _{BE(sat)} | — | 0.93 | 1.1 | V | I _C = 1A, I _B = 100mA |
| Base-Emitter Turn-on Voltage (Note 4) | V _{BE(on)} | — | 0.80 | 1.1 | V | V _{CE} = 2V, I _C = 1A |
| Transition Frequency | f _T | 100 | 250 | — | MHz | V _{CE} = 5V, I _C = 100mA, f = 100MHz |
| Output Capacitance | C _{obo} | — | 9 | 15 | pF | V _{CB} = 10V, f = 1MHz |
| Input Capacitance | C _{ibo} | — | 65 | — | pF | V _{EB} = 5V, f = 1MHz |
| Turn-On Time | t _{on} | — | 57 | — | ns | V _{CC} = 5V, I _C = 500mA, I _{B1} = -I _{B2} = 50mA |
| Delay Time | t _d | — | 19 | — | ns | |
| Rise Time | t _r | — | 38 | — | ns | |
| Turn-Off Time | t _{off} | — | 340 | — | ns | |
| Storage Time | t _s | — | 315 | — | ns | |
| Fall Time | t _f | — | 25 | — | ns | |

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

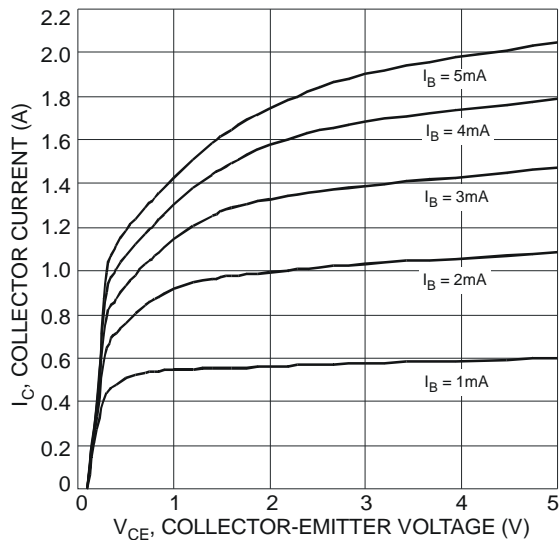


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

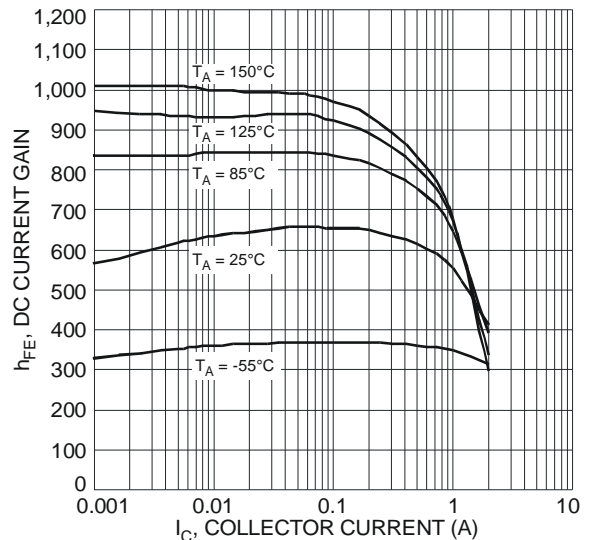


Fig. 5 Typical DC Current Gain vs. Collector Current

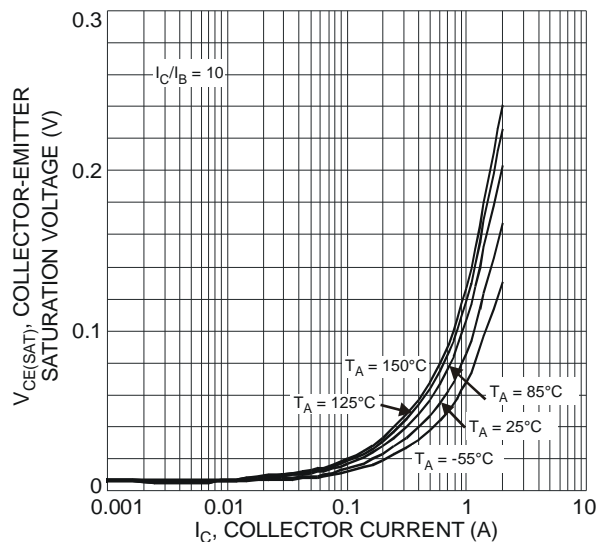


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

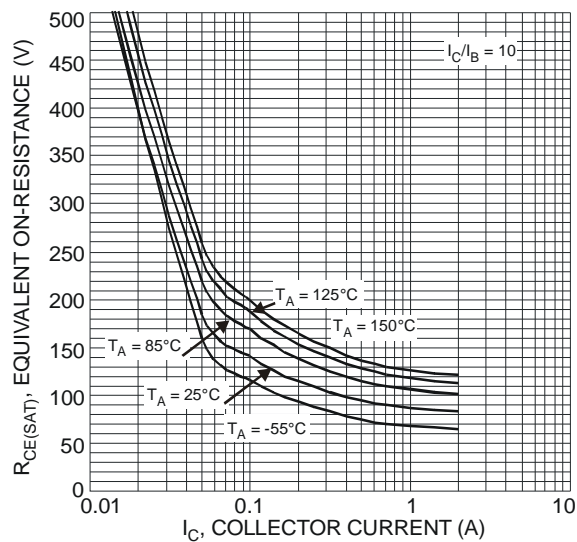


Fig. 7 Typical Equivalent On-Resistance vs. Collector Current

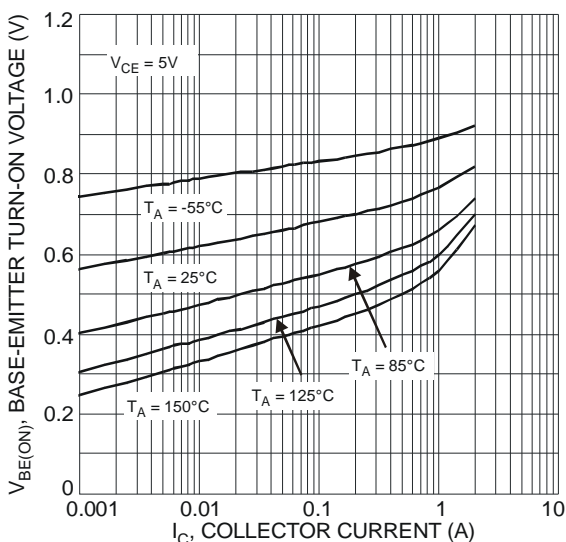


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

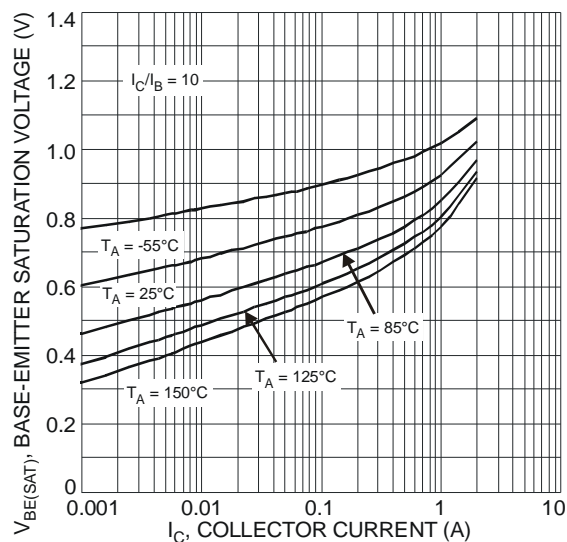


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

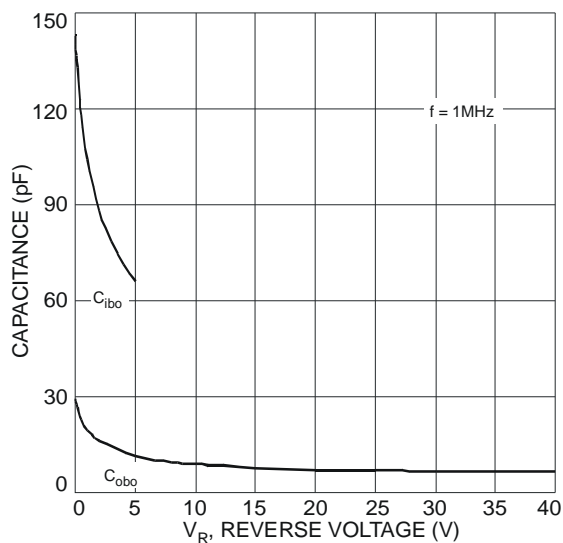
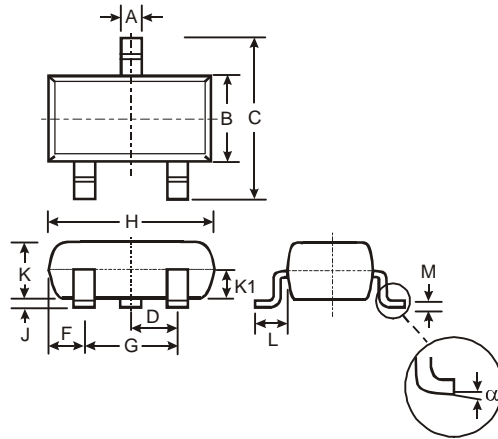


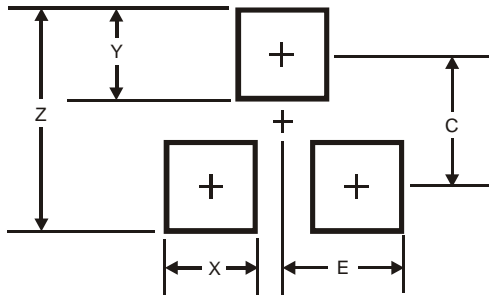
Fig. 10 Typical Capacitance Characteristics

Package Outline Dimensions



| SOT-23 | | | |
|----------------------|-------|------|-------|
| Dim | Min | Max | Typ |
| A | 0.37 | 0.51 | 0.40 |
| B | 1.20 | 1.40 | 1.30 |
| C | 2.30 | 2.50 | 2.40 |
| D | 0.89 | 1.03 | 0.915 |
| F | 0.45 | 0.60 | 0.535 |
| G | 1.78 | 2.05 | 1.83 |
| H | 2.80 | 3.00 | 2.90 |
| J | 0.013 | 0.10 | 0.05 |
| K | 0.903 | 1.10 | 1.00 |
| K1 | - | - | 0.400 |
| L | 0.45 | 0.61 | 0.55 |
| M | 0.085 | 0.18 | 0.11 |
| α | 0° | 8° | - |
| All Dimensions in mm | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| X | 0.8 |
| Y | 0.9 |
| C | 2.0 |
| E | 1.35 |

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